# Міскоснір МСР1790/МСР1791

# 70 mA, High Voltage Regulator

### Features

- 48V (43.5V ±10%) load dump protected for 180ms with a 30 second repetition rate (FORD Test Pulse G Loaded)
- Wide steady state supply voltage, 6.0V 30.0V
- Extended Junction Temperature Range: -40 to +125°C
- Fixed output voltages: 3.0V, 3.3V, 5.0V
- Low quiescent current: 70 µA typical
- Low shutdown quiescent current: 10 µA typical
- Output Voltage Tolerances of ±2.5% over the temperature range
- Maximum output current of 70 mA @ +125°C Junction Temperature
- Maximum continuous input voltage of 30V
- Internal thermal overload protection, +157°C (typical) Junction Temperature
- Internal short circuit current limit, 120 mA (typical) for +5V option.
- Short Circuit Current Foldback
- Shutdown Input option (MCP1791)
- Power Good Output option (MCP1791)
- High PSRR, -90 dB@100 Hz (typical)
- Stable with 1 µF to 1000 µF Tantalum and Electrolytic Capacitors
- Stable with 4.7  $\mu$ F to 1000  $\mu$ F Ceramic Capacitors

### Applications

- Low Voltage A/C powered (24VAC) Fire Alarms, CO<sub>2</sub> Sensors, HVAC Controls
- Automotive Electronics
- Automotive Accessory Power Adapters
- Electronic Thermostat Controls
- Microcontroller power

### **General Description**

The MCP1790/MCP1791 regulator provides up to 70 mA of current. The input operating voltage range is specified from 6.0V to 30V continuous, 48V absolute max, making it ideal for automotive and commercial 12/24 VDC systems.

The MCP1790/MCP1791 has a tight tolerance output voltage load regulation of  $\pm 0.2\%$  (typical) and a very good line regulation at  $\pm 0.0002\%/V$  (typical). The regulator output is stable with ceramic, tantalum, and electrolytic capacitors. The MCP1790/MCP1791 regulator incorporates both thermal and short circuit protection.

The MCP1790 is the 3-pin version of the MCP1790/ MCP1791 family. The MCP1791 is the 5-pin version and incorporates a Shutdown input signal and a Power Good output signal.

The regulator is specifically designed to operate in the automotive environment and will survive +48V (43.5V  $\pm$ 10%) load dump transients and double-battery jumps. The device is designed to meet the stringent quiescent current requirements of the automotive industry. The device is also designed for the commercial low voltage fire alarm/detector systems which use 24 VDC to supply the required alarms throughout buildings. The low ground current, 110 µA (typ.), of the CMOS device will provide a power cost savings to the end users over similar bipolar devices. Typical buildings using hundreds of 24V powered fire and smoke detectors can see substantial savings on energy consumption and wiring gage reduction compared to bipolar regulators.

The MCP1790 device will be offered in the 3-pin DD-PAK, and SOT-223 packages.

The MCP1791 device will be offered in the 5-pin DD-PAK, and SOT-223 packages.

The MCP1790/MCP1791 will have a junction temperature operating range of -40°C to +125°C.

# 1.0 ELECTRICAL CHARACTERISTICS

### Absolute Maximum Ratings †

Input Voltage, V <sub>IN</sub> +48.0V
VIN, PWRGD, $\overline{\text{SHDN}}$ (GND-0.3V) to (V <sub>IN</sub> +0.3V)
VOUT (GND-0.3V) to (+5.5V)
Internal Power Dissipation Internally-Limited (Note 4)
Output Short Circuit CurrentContinuous
Storage temperature55°C to +150°C
Maximum Junction Temperature165°C (Note 7)
Operating Junction Temperature40°C to +125°C
ESD protection on all pins $\ge 6 \text{ kV}$ HBM and $\ge 400 \text{V}$ MM

**†** Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

# AC/DC CHARACTERISTICS

**Electrical Specifications:** Unless otherwise noted,  $V_{IN} = V_{OUT(MAX)} + V_{DROPOUT(MAX)}$ , (Note 1),  $I_{OUT} = 1 \text{ mA}$ ,  $C_{OUT} = 4.7 \ \mu\text{F}$  (X7R Ceramic),  $C_{IN} = 4.7 \ \mu\text{F}$  (X7R Ceramic),  $T_A = +25^{\circ}\text{C}$ , SHDN > 2.4V. Boldface type applies for junction temperatures,  $T_1$  (Note 5) of -40°C to +125°C.

Parameters	Symbol	Min	Тур	Max	Units	Conditions
Input Operating Voltage	V <sub>IN</sub>	6.0	_	30.0	V	+48V <sub>DC</sub> Load Dump Peak < 500 ms
Input Quiescent Current	lq	_	70	130	μA	I <sub>L</sub> = 0 mA
Input Quiescent Current for SHDN Mode	ISHDN	_	10	25	μA	SHDN = GND
Ground Current	I <sub>GND</sub>	_	110	210	μA	I <sub>L</sub> = 70 mA
Maximum Output Current	I <sub>OUT</sub>	70	_	_	mA	
Line Regulation	ΔV <sub>OUT</sub> / (V <sub>OUT</sub> XΔV <sub>IN</sub> )	_	±0.0002	±0.05	%/V	6.0V < V <sub>IN</sub> < 30V
Load Regulation	ΔV <sub>OUT</sub> /V <sub>OUT</sub>	-0.45	±0.2	0.45	%	I <sub>OUT</sub> = 1 mA to 70 mA (Note 3)
Output Peak Short Circuit Current	I <sub>OUT_SC</sub>	_	V <sub>R</sub> /10	—	A	R <sub>LOAD</sub> < 0.1 Ω, Peak Current
Output Voltage Regulation	V <sub>OUT</sub>	V <sub>R</sub> -2.5%	V <sub>R</sub>	V <sub>R</sub> +2.5%	V	6.0V < V <sub>IN</sub> < 30V
V <sub>OUT</sub> Temperature Coefficient	TCV <sub>OUT</sub>	_	65	_	ppm/°C	Note 9
Input Voltage to Turn On Output	V <sub>ON</sub>	_	5.5	6.0	V	Rising V <sub>IN</sub>

Note 1: The minimum  $V_{IN}$ ,  $V_{IN(MIN)}$  must meet two conditions:  $V_{IN} \ge 6.0V$  and  $V_{IN} \ge V_{OUT(MAX)} + V_{DROPOUT(MAX)}$ .

**2:** V<sub>R</sub> is the nominal regulator output voltage.

- **3:** Load regulation is measured at a constant junction temperature using low duty cycle pulse testing. Load regulation is tested over a load range from 1 mA to the maximum specified output current.
- 4: The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air. (i.e., T<sub>A</sub>, T<sub>J</sub>, θ<sub>JA</sub>). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum 165°C rating. Sustained junction temperatures above 165°C can impact the device reliability.
- 5: The junction temperature is approximated by soaking the device under test at an ambient temperature equal to the desired Junction temperature. The test time is small enough such that the rise in the Junction temperature over the ambient temperature is not significant.
- **6:** Dropout voltage is defined as the input-to-output voltage differential at which the output voltage drops 2% below its nominal value that was measured with an input voltage of  $V_{IN} = V_R + V_{DROPOUT(MAX)}$ .
- 7: Sustained junction temperatures above 165°C can impact the device reliability.
- 8: The Short Circuit Recovery Time test is done by placing the device into a short circuit condition and then removing the short circuit condition before the device die temperature reaches 125 °C. If the device goes into thermal shutdown, then the Short Circuit Recovery Time will depend upon the thermal dissipation properties of the package and circuit board.
- 9: TCV<sub>OUT</sub> = (V<sub>OUT-HIGH</sub> V<sub>OUT-LOW</sub>) \*10^6 / (V<sub>R</sub> \* ∆Temperature), V<sub>OUT-HIGH</sub> = highest voltage measured over the temperaturerange. V<sub>OUT-LOW</sub> = lowest voltage measured over the temperature range.

# **AC/DC CHARACTERISTICS (CONTINUED)**

**Electrical Specifications:** Unless otherwise noted,  $V_{IN} = V_{OUT(MAX)} + V_{DROPOUT(MAX)}$ , (Note 1),  $I_{OUT} = 1 \text{ mA}$ ,  $C_{OUT} = 4.7 \mu F$  (X7R Ceramic),  $C_{IN} = 4.7 \mu F$  (X7R Ceramic),  $T_A = +25^{\circ}C$ , SHDN > 2.4V. Boldface type applies for junction temperatures,  $T_{.1}$  (Note 5) of -40°C to +125°C.

Parameters	Symbol	Min	Тур	Max	Units	Conditions
Short Circuit Foldback Voltage Corner	V <sub>FOLDBACK</sub>	_	4.2	—	V	$V_R = 5.0V$ Falling V <sub>OUT</sub> , R <sub>LOAD</sub> < 0.1 Ω
		_	3.0	—	V	V <sub>R</sub> = 3.3V Falling V <sub>OUT,</sub> R <sub>LOAD</sub> < 0.1 Ω
		—	2.7	—	V	$V_R = 3.0V$ Falling V <sub>OUT,</sub> R <sub>LOAD</sub> < 0.1 Ω
Short Circuit Foldback Current		—	105	—	mA	V <sub>OUT</sub> ~= 0V, R <sub>LOAD</sub> < 0.1 Ω, V <sub>R</sub> = 5.0V <b>(Note 2)</b>
		—	99	—	mA	V <sub>R</sub> = 3.3V (Note 2)
		_	99	—	mA	V <sub>R</sub> = 3.0V (Note 2)
Startup Voltage Overshoot	V <sub>OVER</sub>	_	0.10	_	% V <sub>OUT</sub>	$V_{IN} = 0V$ to 6.0V
Dropout Voltage	V <sub>DROPOUT</sub>	_	700	1300	mV	I <sub>OUT</sub> = 70 mA, (Note 6)
Dropout Current	I <sub>DO</sub>	_	130	_	μA	V <sub>R</sub> = 5.0V, V <sub>IN</sub> = 4.500V
I <sub>OUT</sub> = 0 mA		_	75	_	μA	V <sub>R</sub> = 3.3V, V <sub>IN</sub> = 4.500V
		_	75	_	μA	V <sub>R</sub> = 3.0V, V <sub>IN</sub> = 4.500V
Shutdown Input						
Logic High Input	V <sub>SHDN-HIGH</sub>	2.4	_	V <sub>IN(MAX)</sub>	V	
Logic Low Input	V <sub>SHDN-LOW</sub>	0	_	0.8	V	
Shutdown Input Leakage Current	SHDN <sub>ILK</sub>	_	0.100 3.0	0.500 5.0	μA	SHDN = GND SHDN = 6V
Power Good Characteristics						
PWRGD Input Voltage Operating Range	V <sub>PWRGD_VIN</sub>	2.8	—	—	V	
PWRGD Threshold Voltage (Referenced to V <sub>OUT)</sub>	V <sub>PWRGD_TH</sub>	88	90	92	%V <sub>OUT</sub>	Falling Edge of V <sub>OUT</sub>
PWRGD Threshold Hysteresis	V <sub>PWRGD_HYS</sub>	1.0	2.0	3.0	%V <sub>OUT</sub>	Rising Edge of V <sub>OUT</sub>
PWRGD Output Voltage LOW	V <sub>PWRGD_L</sub>	—	0.2	0.4	V	$I_{PWRGD SINK} = 5.0 \text{ mA},$ $V_{OUT} = 0V$
PWRGD Output Sink Current	I <sub>PWRGD_L</sub>	5.0	_	—	mA	V <sub>PWRGD</sub> <= 0.4V
PWRGD Leakage	I <sub>PWRGD_LK</sub>	_	1.0	_	nA	$V_{PWRGD} = V_{IN} = 6.0V$
PWRGD Time Delay	T <sub>PG</sub>		30	_	μs	Rising Edge

Note 1: The minimum  $V_{IN}$ ,  $V_{IN(MIN)}$  must meet two conditions:  $V_{IN} \ge 6.0V$  and  $V_{IN} \ge V_{OUT(MAX)} + V_{DROPOUT(MAX)}$ .

**2:** V<sub>R</sub> is the nominal regulator output voltage.

- **3:** Load regulation is measured at a constant junction temperature using low duty cycle pulse testing. Load regulation is tested over a load range from 1 mA to the maximum specified output current.
- 4: The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air. (i.e., T<sub>A</sub>, T<sub>J</sub>, θ<sub>JA</sub>). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum 165°C rating. Sustained junction temperatures above 165°C can impact the device reliability.
- 5: The junction temperature is approximated by soaking the device under test at an ambient temperature equal to the desired Junction temperature. The test time is small enough such that the rise in the Junction temperature over the ambient temperature is not significant.
- **6:** Dropout voltage is defined as the input-to-output voltage differential at which the output voltage drops 2% below its nominal value that was measured with an input voltage of  $V_{IN} = V_R + V_{DROPOUT(MAX)}$ .
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- 8: The Short Circuit Recovery Time test is done by placing the device into a short circuit condition and then removing the short circuit condition before the device die temperature reaches 125 °C. If the device goes into thermal shutdown, then the Short Circuit Recovery Time will depend upon the thermal dissipation properties of the package and circuit board.
- 9: TCV<sub>OUT</sub> = (V<sub>OUT-HIGH</sub> V<sub>OUT-LOW</sub>) \*10<sup>6</sup> / (V<sub>R</sub> \* ΔTemperature), V<sub>OUT-HIGH</sub> = highest voltage measured over the temperaturerange.

# AC/DC CHARACTERISTICS (CONTINUED)

**Electrical Specifications:** Unless otherwise noted,  $V_{IN} = V_{OUT(MAX)} + V_{DROPOUT(MAX)}$ , (Note 1),  $I_{OUT} = 1 \text{ mA}$ ,  $C_{OUT} = 4.7 \mu \text{F}$  (X7R Ceramic),  $C_{IN} = 4.7 \mu \text{F}$  (X7R Ceramic),  $T_A = +25^{\circ}\text{C}$ , SHDN > 2.4V. Boldface type applies for junction temperatures,  $T_{.1}$  (Note 5) of -40°C to +125°C.

Parameters	Symbol	Min	Тур	Max	Units	Conditions
Detect Threshold to PWRGD Active Time Delay	TV <sub>DET-PWRG</sub> D		235	_	μs	$V_{OUT} = V_{PWRGD_TH} +$ 100 mV to $V_{PWRGD_TH} -$ 100 mV
AC Performance						
Output Delay From SHDN	T <sub>OR</sub>	_	200	—	μs	$\label{eq:shdn} \begin{array}{l} \hline \textbf{SHDN} = \textbf{GND} \text{ to } \textbf{V}_{\text{IN},} \\ \textbf{V}_{\text{OUT}} = \textbf{GND} \text{ to } 95\% \textbf{V}_{\text{R},} \\ \textbf{C}_{\text{OUT}} = 1.0 \ \mu\text{F} \end{array}$
PWRGD Delay from SHDN	T <sub>SHDN_PG</sub>	_	400	—	ns	$\overline{SHDN} = V_{IN} \text{ to GND}_{,}$ $C_{OUT} = 1.0  \mu F$
Output Noise	e <sub>N</sub>		1.2	—	µV/√Hz)	$I_{OUT} = 50 \text{ mA}, \text{ f} = 1 \text{ kHz}$
Power Supply Ripple Rejection Ratio	PSRR				dB	$V_{IN} = 7.0V, C_{IN} = 0 \ \mu F,$ $I_{OUT} = 10 \ mA,$ $V_{INAC} = 400 \ mVpp$
		—	90	—		f = 100 Hz
		—	75	—		f = 1 kHz, V <sub>R</sub> = 5.0V
		—	80	—		f = 1 kHz, V <sub>R</sub> = < 5.0V
Thermal Shutdown Temperature	T <sub>SD</sub>		157	_	°C	Rising Temperature
Thermal Shutdown Hysteresis	$\Delta T_{SD}$	_	20	—	°C	Falling Temperature
Short Circuit Recovery Time	t <sub>THERM</sub>	_	0	—	ms	(Note 8)

Note 1: The minimum  $V_{IN}$ ,  $V_{IN(MIN)}$  must meet two conditions:  $V_{IN} \ge 6.0V$  and  $V_{IN} \ge V_{OUT(MAX)} + V_{DROPOUT(MAX)}$ .

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**3:** Load regulation is measured at a constant junction temperature using low duty cycle pulse testing. Load regulation is tested over a load range from 1 mA to the maximum specified output current.

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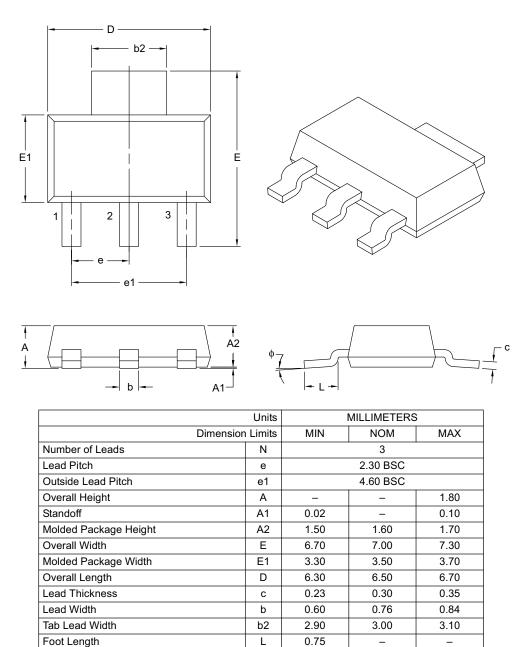
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9: TCV<sub>OUT</sub> = (V<sub>OUT-HIGH</sub> - V<sub>OUT-LOW</sub>) \*10<sup>6</sup> / (V<sub>R</sub> \* ΔTemperature), V<sub>OUT-HIGH</sub> = highest voltage measured over the temperaturerange.

# **TEMPERATURE SPECIFICATIONS**

Parameters	Symbol	Min	Тур	Max	Units	Conditions
Temperature Ranges						
Specified Temperature Range	TJ	-40		+125	°C	
Operating Temperature Range	Τ <sub>J</sub>	-40		+125	°C	
Storage Temperature Range	Т <sub>Ј</sub>	-55		+150	°C	
Package Thermal Resistances						
Thermal Resistance, 3LD DDPAK	$\theta_{JA}$ $\theta_{JC}$	—	31.4 3	—	°C/W	EIA/JEDEC JESD51-751-7 4 Layer Board
Thermal Resistance, 3LD SOT-223	$\theta_{JA}$ $\theta_{JC}$	—	62 15	—	°C/W	EIA/JEDEC JESD51-751-7 4 Layer Board
Thermal Resistance, 5LD DDPAK	$\theta_{JA}$ $\theta_{JC}$	—	31.4 3	—	°C/W	EIA/JEDEC JESD51-751-7 4 Layer Board
Thermal Resistance, 5LD SOT-223	$\theta_{JA}$ $\theta_{JC}$	—	62 15	—	°C/W	EIA/JEDEC JESD51-751-7 4 Layer Board

## 3-Lead Plastic Small Outline Transistor (DB) [SOT-223]



### Notes:

1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.

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2. Dimensioning and tolerancing per ASME Y14.5M.

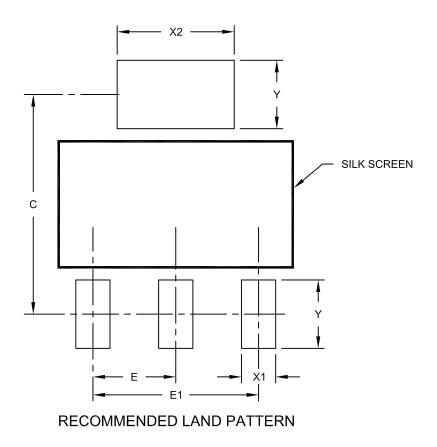
Lead Angle

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-032B

10°

3-Lead Plastic Small Outline Transistor (DB) [SOT-223]



		Units	Ν	MILLIMETERS		
	Dimension	Limits	MIN	NOM	MAX	
Contact Pitch	E			2.30 BSC		
Overall Pitch		E1		4.60 BSC		
Contact Pad Spacing		С		6.10		
Contact Pad Width		X1			0.95	
Contact Pad Width		X2			3.25	
Contact Pad Length		Ý			1.90	

### Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2032A

# **PRODUCT IDENTIFICATION SYSTEM**

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

<u>PART NO. XX</u>	<u>× × × ×</u>	Examples:
	 Feature Tolerance Temp. Package	<ul> <li>a) MCP1790-3002E/EB:3.0V LDO Regulator, 3LD DDPAK</li> <li>b) MCP1790-3302E/EB:3.3V LDO Regulator, 3LD DDPAK</li> </ul>
Device:	MCP1790: 70 mA High Voltage Regulator MCP1790T: 70 mA High Voltage Regulator	c) MCP1790-5002E/EB:5.0V LDO Regulator, 3LD DDPAK
	Tape and Reel MCP1791: 70 mA High Voltage Regulator	d) MCP1790-3002E/DB:3.0V LDO Regulator, 3LD SOT-223
	MCP1791T: 70 mA High Voltage Regulator Tape and Reel	e) MCP1790-3302E/DB:3.3V LDO Regulator, 3LD SOT-223
Output Voltage *:	30 = 3.0V "Standard" 33 = 3.3V "Standard" 50 = 5.0V "Standard"	f) MCP1790-5002E/DB:5.0V LDO Regulator, 3LD SOT-223
Extra Feature Code:	*Contact factory for other output voltage options 0 = Fixed	a) MCP1791-3002E/ET: 3.0V LDO Regulator 5LD DDPAK
		b) MCP1791-3302E/ET 3.3V LDO Regulator 5LD DDPAK
Tolerance:	2 = 2.5% (Standard)	c) MCP1791-5002E/ET: 5.0V LDO Regulator 5LD DDPAK
Temperature:	$E = -40^{\circ}C \text{ to } +125^{\circ}C$	d) MCP1791-3002E/DC 3.0V LDO Regulator 5LD SOT-223
Package Type:	EB = Plastic, DDPAK, 3-lead ET = Plastic, DDPAK, 5-lead	e) MCP1791-3302E/DC 3.3V LDO Regulator 5LD SOT-223
	DB = Plastic Transistor Outline, SOT-223, 3-lead DC = Plastic Transistor Outline, SOT-223, 5-lead	f) MCP1791-5002E/DC 5.0V LDO Regulator 5LD SOT-223